μPD431000A
131,072 x 8-Bit
Static CMOS RAM

Description

The μPD431000A is a 131,072-word by 8-bit static RAM fabricated with advanced silicon-gate technology. CMOS peripheral circuits and N-channel memory cells with polysilicon resistors make the μPD431000A a high-speed device that requires very low power and no clock or refreshing.

Minimum standby power is drawn when CE_2 is low, independent of the other inputs' levels. Data retention is guaranteed at a power supply voltage as low as 2 volts. The μPD431000A is available in standard 32-pin plastic DIP, 32-pin plastic miniflat, and 32-pin plastic TSOP packaging.

Features

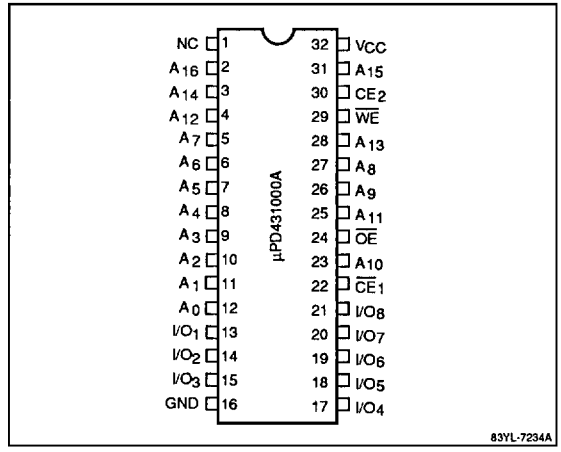
- 131,072-word by 8-bit organization
- Single + 5-volt power supply
- Fully static operation—no clock or refreshing
- TTL-compatible inputs and outputs
- Common I/O using three-state outputs
- Two CE pins and one $\overline{OE}$ pin for easy application
- Data retention current of 0.5 μA typical
- Data retention voltage of 2 V minimum
- Standard 32-pin plastic DIP, miniflat, and TSOP packaging

Pin Identification

Symbol	Function
A_0 - A_{16}	Address inputs
I/O_0 - I/O_7	Data inputs/outputs
$\overline{CE_1}$ and CE_2	Chip enables 1 and 2
$\overline{OE}$	Output enable
$\overline{WE}$	Write enable
GND	Ground
V_{CC}	+5-volt power supply
NC	No connection

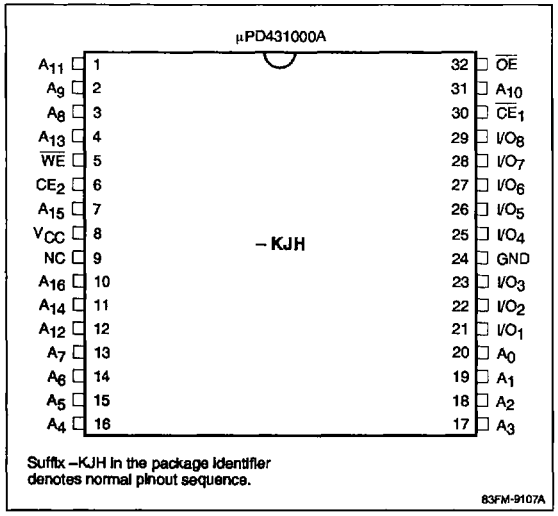
Pin Configurations

32-Pin Plastic DIP or Miniflat



Pin Configurations (cont)

32-Pin Plastic TSOP (Normal Pinouts)



Suffix –KJH in the package identifier denotes normal pinout sequence.

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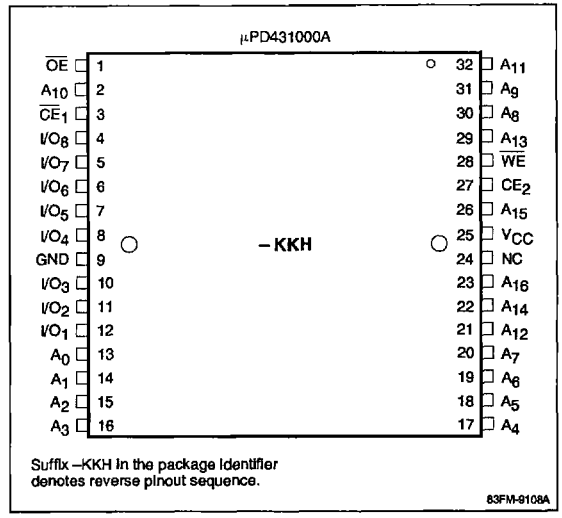
32-Pin Plastic TSOP (Reverse Pinouts)



Suffix –KKH in the package identifier denotes reverse pinout sequence.

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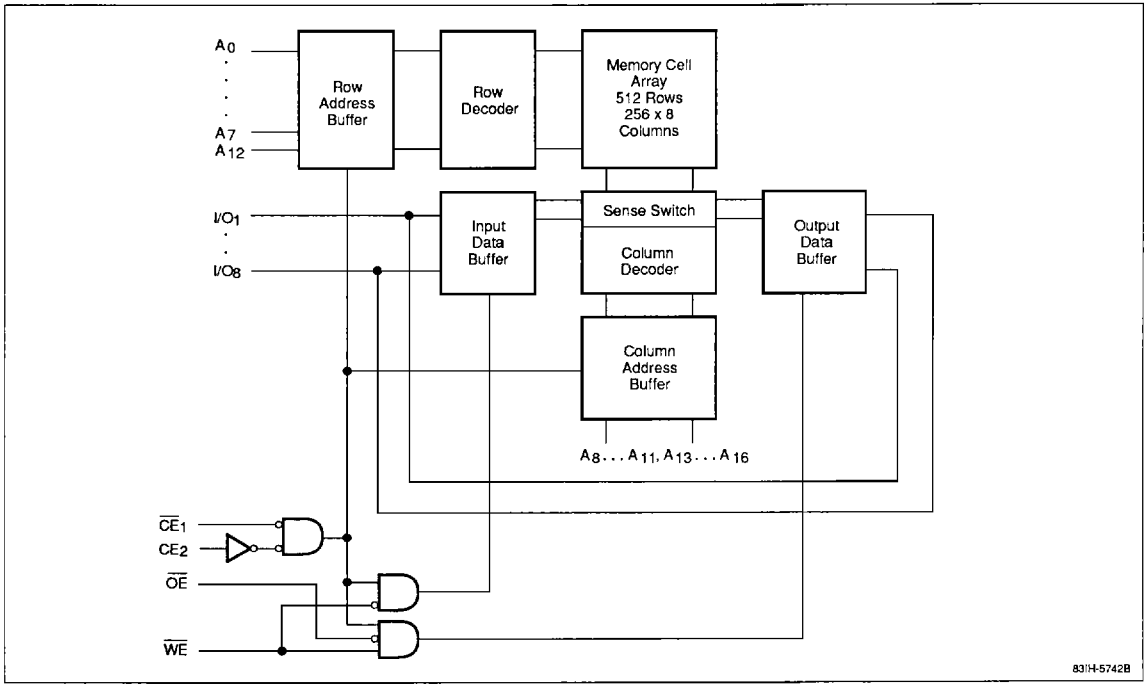
Block Diagram



Absolute Maximum Ratings

Supply voltage, V_{CC} (Note 1)	−0.5 to +7.0 V
Input voltage, V_{IN} (Note 1)	−0.5 to V_{CC} + 0.5 V
Output voltage, $V_{I/O}$ (Note 1)	−0.5 to V_{CC} + 0.5 V
Operating temperature, T_{OPR}	0 to +70°C
Storage temperature, T_{STG}	−55 to +125°C
Power dissipation, P_D	1.0 W

Exposure to Absolute Maximum Ratings for extended periods may affect device reliability; exceeding the ratings could cause permanent damage. The device should be operated within the limits specified under DC and AC Characteristics.

Notes:

(1) −3.0 V minimum (pulse width = 50 ns).

Capacitance

T_A = +25°C; f = 1 MHz; V_{IN} and V_{OUT} = 0 V

Parameter	Symbol	Min	Typ	Max	Unit
Input capacitance	C_I			6	pF
Input/output capacitance	$C_{I/O}$			10	pF

Notes:

(1) This parameter is sampled and not 100% tested.

Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
Input voltage, low	V_{IL}	−0.3		0.8	V
Input voltage, high	V_{IH}	2.2		V_{CC} + 0.5	V
Ambient temperature	T_A	0		70	°C

Notes:

(1) −3.0 V minimum (pulse width = 50 ns).

Truth Table

Function	$\overline{CE_1}$	CE_2	$\overline{OE}$	$\overline{WE}$	I/O	I_{CC}
Not selected	H	X	X	X	High-Z	Standby
Not selected	X	L	X	X	High-Z	Standby
Selected	L	H	H	H	High-Z	Active
Read	L	H	L	H	D_{OUT}	Active
Write	L	H	X	L	D_{IN}	Active

Notes:

(1) X = don't care.

Ordering Information

Catalog Part Number	Access Time (max)	I_{SB1} (max)	Package
μPD431000ACZ-70L	70 ns	0.1 mA	32-pin plastic DIP
CZ-85L	85 ns		
CZ-10L	100 ns		
μPD431000ACZ-70LL	70 ns	0.05 mA	
CZ-85LL	85 ns		
CZ-10LL	100 ns		
μPD431000AGW-70L	70 ns	0.1 mA	32-pin plastic miniflat
GW-85L	85 ns		
GW-10L	100 ns		
μPD431000AGW-70LL	70 ns	0.05 mA	
GW-85LL	85 ns		
GW-10LL	100 ns		
μPD431000AGZ-70L	70 ns	0.1 mA	32-pin plastic TSOP (normal pinouts)
GZ-85L	85 ns		
GZ-10L	100 ns		
μPD431000AGZ-70LL	70 ns	0.05 mA	
GZ-85LL	85 ns		
GZ-10LL	100 ns		
μPD431000AGZM-70L	70 ns	0.1 mA	32-pin plastic TSOP (reverse pinouts)
GZM-85L	85 ns		
GZM-10L	100 ns		
μPD431000AGZM-70LL	70 ns	0.05 mA	
GZM-85LL	85 ns		
GZM-10LL	100 ns		

DC Characteristics

T_A = 0 to +70°C; V_{CC} = +5.0 V ± 10%

		-L Version			-LL Version				
Parameter	**Symbol**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**	**Test Conditions**
Input leakage current	I_{LI}	−1		1	-1		1	μA	V_{IN} = 0 V to V_{CC}
I/O leakage current	I_{LO}	−1		1	-1		1	μA	$V_{I/O}$ = 0 V to V_{CC}; $\overline{CE}_1$ = V_{IH}, or CE_2 = V_{IL}, or $\overline{OE}$ = V_{IH}, or $\overline{WE}$ = V_{IL}
Operating supply current	I_{CCA1}		40	70		40	70	mA	$\overline{CE}_1$ = V_{IL}; CE_2 = V_{IH}; t_{RC} = t_{RC} (min); $I_{I/O}$ = 0 mA
	I_{CCA2}			15			15	mA	$\overline{CE}_1$ = V_{IL}; CE_2 = V_{IH}; $I_{I/O}$ = 0 mA
	I_{CCA3}			10			10	mA	$V_{CE1} \leq 0.2$ V; $V_{CE2} \geq V_{CC} - 0.2$ V; t_{RC} or t_{WC} = 1 MHz; $V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V
Standby supply current	I_{SB}			3			3	mA	$\overline{CE}_1$ = V_{IH} or CE_2 = V_{IL} (Note 1)
	I_{SB1}		0.002	0.1		0.001	0.05	mA	$\overline{CE}_1$ and $CE_2 \geq V_{CC} - 0.2$ V (Note 2)
	I_{SB2}		0.002	0.1		0.001	0.05	mA	$CE_2 \leq 0.2$ V (Note 2)
Output voltage, low	V_{OL}			0.4			0.4	V	I_{OL} = 2.1 mA
Output voltage, high	V_{OH}	2.4			2.4			V	I_{OH} = −1.0 mA

AC Characteristics

T_A = 0 to +70°C; V_{CC} = +5.0 V ± 10%

Parameter	Symbol	μPD431000A-70		μPD431000A-85		μPD431000A-10		Unit	Test Conditions
		Min	Max	Min	Max	Min	Max		
Read Operation									
Read cycle time	t_{RC}	70		85		100		ns	
Address access time	t_{AA}		70		85		100	ns	(Note 2)
$\overline{CE}_1$ access time	t_{CO1}		70		85		100	ns	(Note 2)
CE_2 access time	t_{CO2}		70		85		100	ns	(Note 2)
Output enable to output valid	t_{OE}		35		45		50	ns	(Note 2)
Output hold from address change	t_{OH}	10		10		10		ns	
$\overline{CE}_1$ to output in low-Z	t_{LZ1}	10		10		10		ns	(Note 3)
CE_2 to output in low-Z	t_{LZ2}	10		10		10		ns	(Note 3)
Output enable to output in low-Z	t_{OLZ}	5		5		5		ns	(Note 3)
$\overline{CE}_1$ to output in high-Z	t_{HZ1}		25		30		35	ns	(Note 3)
CE_2 to output in high-Z	t_{HZ2}		25		30		35	ns	(Note 3)
Output enable to output in high-Z	t_{OHZ}		25		30		35	ns	(Note 3)
Write Operation									
Write cycle time	t_{WC}	70		85		100		ns	
$\overline{CE}_1$ to end of write	t_{CW1}	55		70		85		ns	
CE_2 to end of write	t_{CW2}	55		70		85		ns	
Address valid to end of write	t_{AW}	55		70		85		ns	
Address setup time	t_{AS}	0		0		0		ns	
Write pulse width	t_{WP}	50		60		70		ns	
Write recovery time	t_{WR}	5		5		5		ns	
Data valid to end of write	t_{DW}	35		35		40		ns	
Data hold time	t_{DH}	0		0		0		ns	
Write enable to output in high-Z	t_{WHZ}		25		30		35	ns	(Note 3)
Output active from end of write	t_{OW}	5		5		5		ns	(Note 3)

Notes:

(1) Input pulse levels = 0.8 to 2.2 V; input rise and fall times = 5 ns; timing reference levels = 1.5 V.

(2) See figure 1 for output loading.

(3) See figure 2 for output loading.

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Figure 1. Output Loading

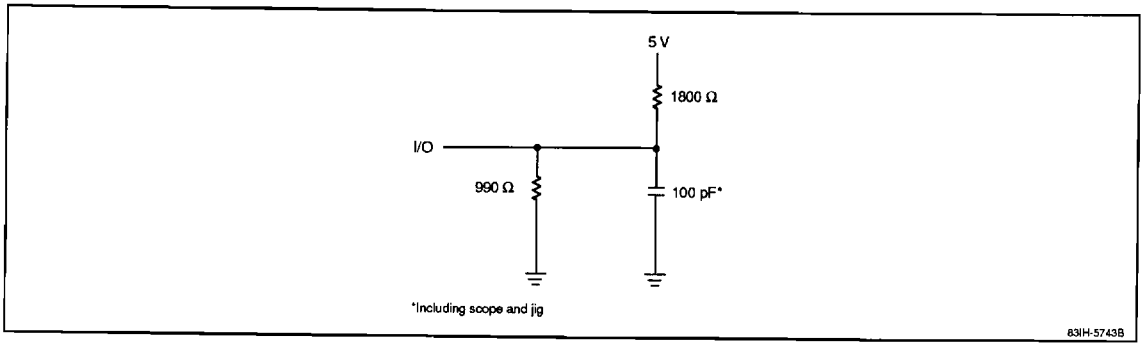
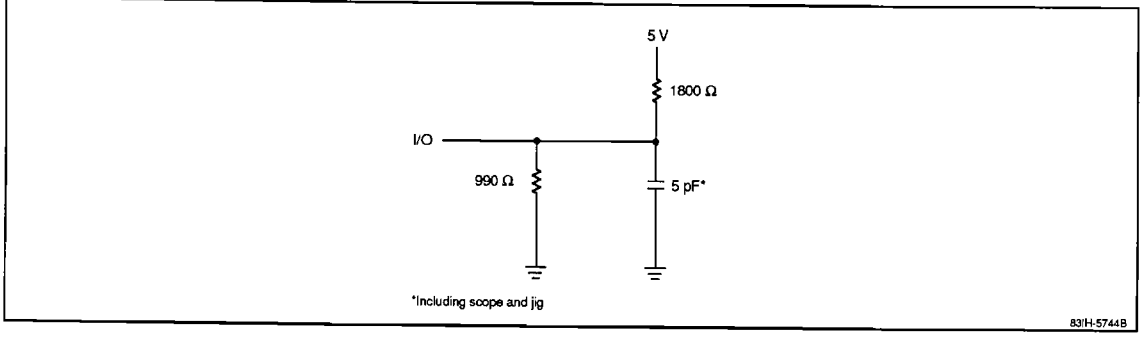


Figure 2. Output Loading for t_{HZ1}, t_{HZ2}, t_{LZ1}, t_{LZ2}, t_{OLZ}, t_{OHZ}, t_{OW}, and t_{WHZ}



Low V_{CC} Data Retention Characteristics

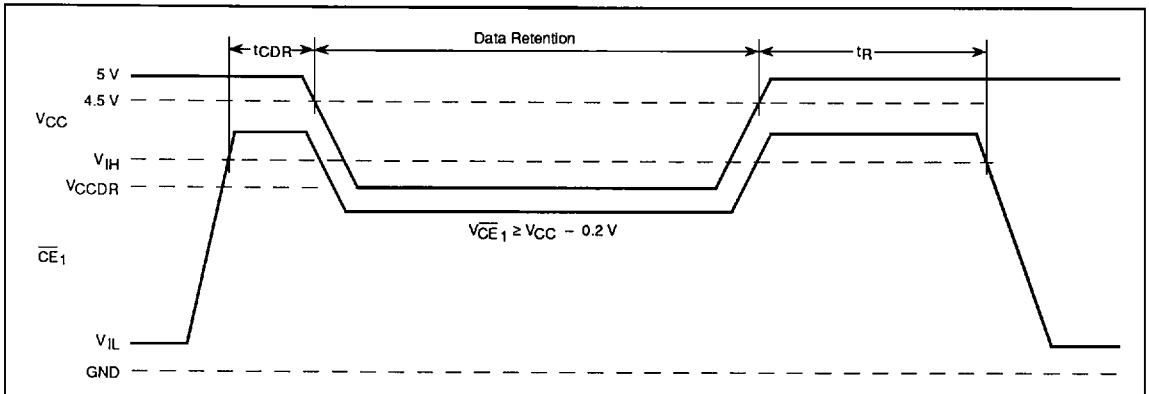
T_A = 0 to +70°C

Parameter	Symbol	-L Version Min	-L Version Typ	-L Version Max	-LL Version Min	-LL Version Typ	-LL Version Max	Unit	Test Conditions
Data retention supply voltage	V_{CCDR1}	2		5.5	2		5.5	V	$\overline{CE}_1 \geq V_{CC} - 0.2$ V; $CE_2 \geq V_{CC} - 0.2$ V or $CE_2 \leq 0.2$ V
	V_{CCDR2}	2		5.5	2		5.5	V	$CE_2 \leq 0.2$ V
Data retention supply current	I_{CCDR1}		1	50		0.5	20	μA	V_{CC} = 3.0 V; $\overline{CE}_1 \geq V_{CC} - 0.2$ V; $CE_2 \geq V_{CC} - 0.2$ V or $CE_2 \leq 0.2$ V (Note 1)
	I_{CCDR2}		1	50		0.5	20	μA	V_{CC} = 3.0 V; $CE_2 \leq 0.2$ V (Note 1)
Chip deselection to data retention	t_{CDR}	0			0			ns	
Operation recovery time	t_R	5			5			ms	

Notes:

(1) At 0 to 40°C, the maximum for I_{CCDR1} and I_{CCDR2} is 15 μA for the -L version and 3 μA for the -LL version.

Figure 3. $\overline{CE_1}$-Controlled Data Retention Timing



Note:
[1] CE_2 must be equal to or higher than V_{CC} − 0.2 V, or equal to or lower than 0.2 V.
The other inputs (Addresses, $\overline{OE}$, $\overline{WE}$, I/Os) can be in high impedance.

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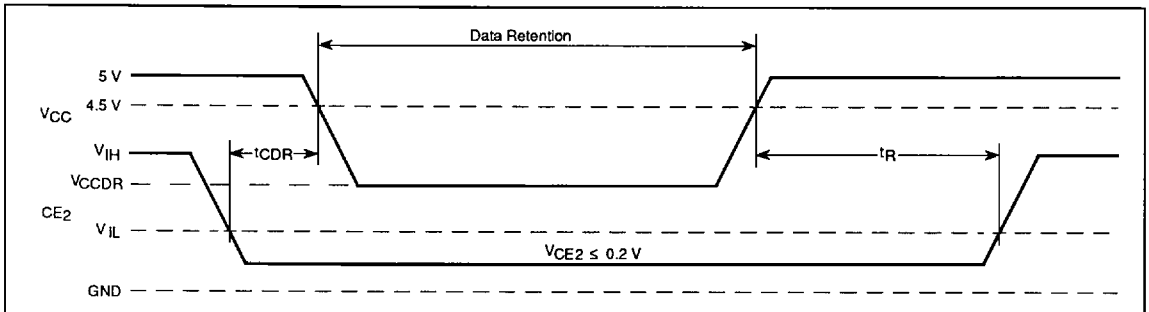
Figure 4. CE_2-Controlled Data Retention Timing



Note:
[1] The other inputs (Addresses, $\overline{CE_1}$, $\overline{OE}$, $\overline{WE}$, I/Os) can be in high impedance.

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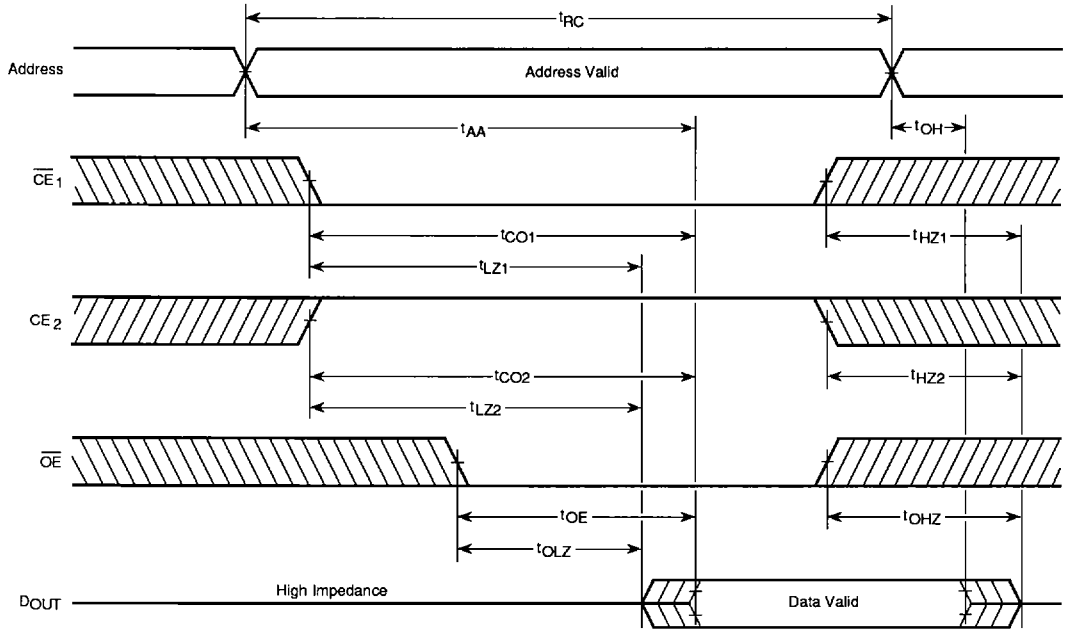
Timing Waveforms

Read Cycle



Notes:

[1] $\overline{WE}$ is high for a read cycle.

[2] Address valid prior to or coincident with the latter of the low transition of $\overline{CE}_1$ or the high transition of CE_2.

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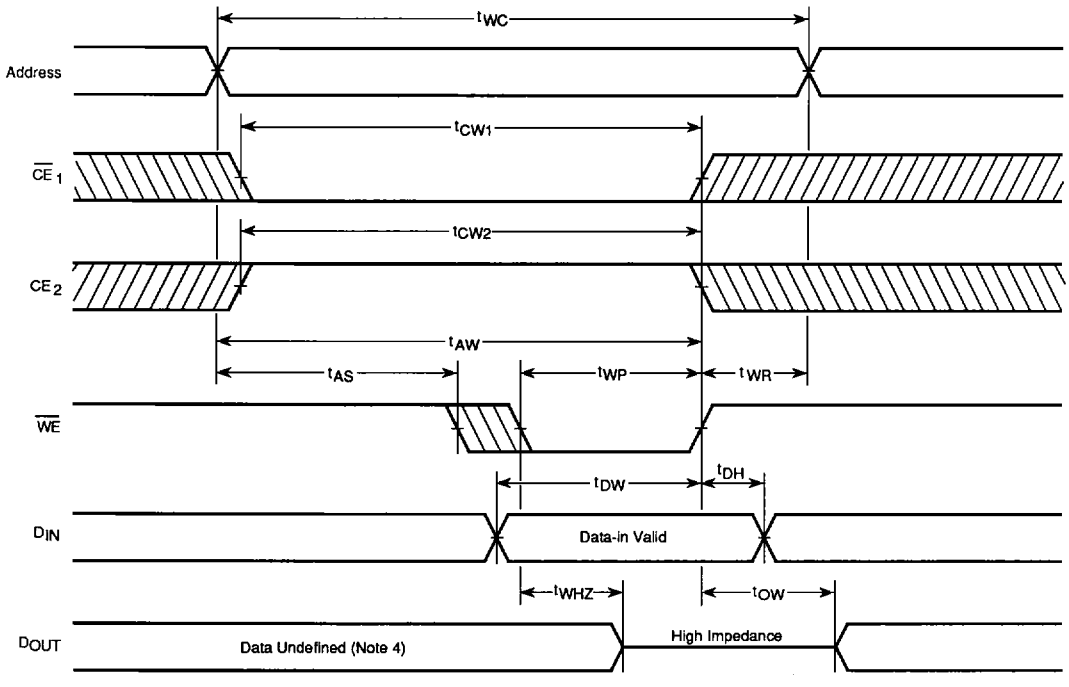
Timing Waveforms (cont)

$\overline{WE}$-Controlled Write Cycle



Notes:

[1] A write cycle occurs during the overlap of a low $\overline{CE}_1$ and $\overline{WE}$ and a high CE_2.

[2] $\overline{CE}_1$ or $\overline{WE}$ must be high or CE_2 must be low during address transition.

[3] If $\overline{OE}$ is high, the I/O pins remain in high impedance.

[4] During this period, the I/O pins may be in the output state; therefore, input signals of opposite phase to the output must not be applied.

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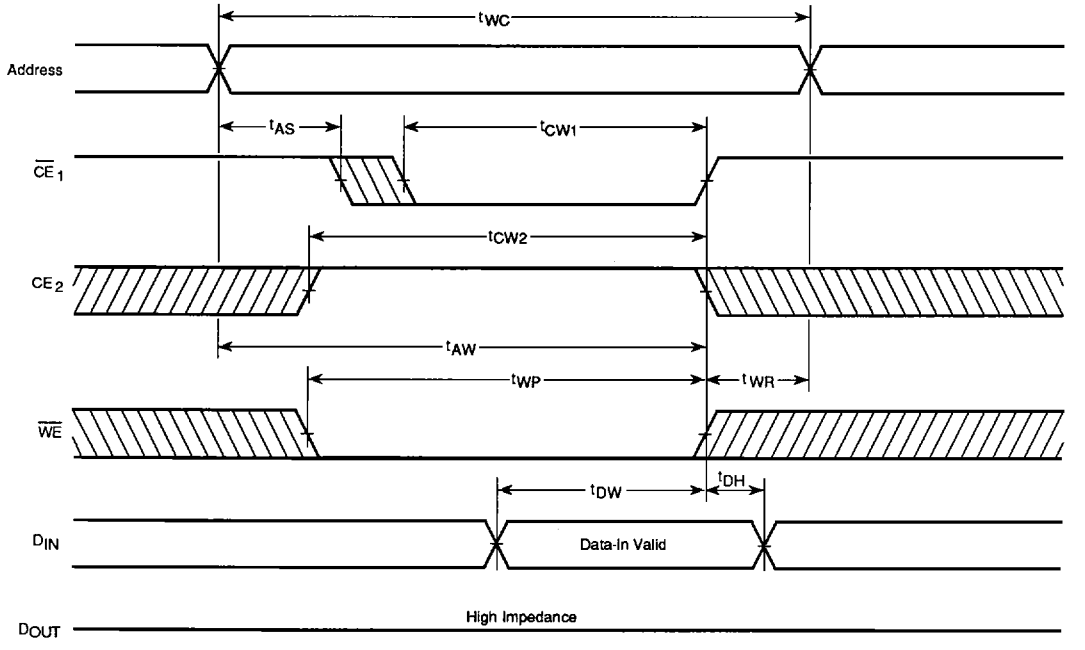
Timing Waveforms (cont)

$\overline{CE_1}$-Controlled Write Cycle



Notes:

[1] A write cycle occurs during the overlap of a low $\overline{CE_1}$ and $\overline{WE}$ and a high CE_2.

[2] $\overline{CE_1}$ or $\overline{WE}$ must be high or CE_2 must be low during address transition.

[3] If $\overline{OE}$ is high, the I/O pins remain in high impedance.

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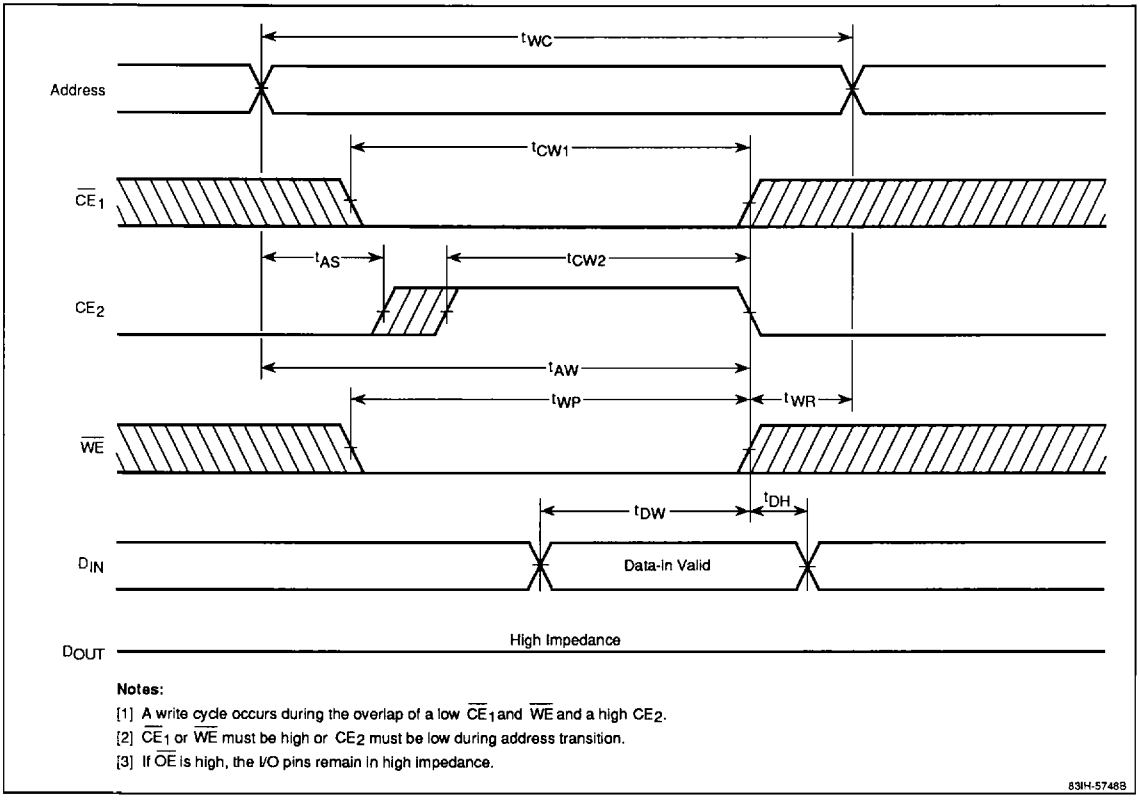
Timing Waveforms (cont)

CE_2-Controlled Write Cycle



Notes:

[1] A write cycle occurs during the overlap of a low $\overline{CE}_1$ and $\overline{WE}$ and a high CE_2.

[2] $\overline{CE}_1$ or $\overline{WE}$ must be high or CE_2 must be low during address transition.

[3] If $\overline{OE}$ is high, the I/O pins remain in high impedance.

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